



## In situ photoemission electron spectroscopy study of nitrogen ion implanted AISI-H13 steel

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### Abstract

In this paper we report the effect of hydrogen on the structural properties of AISI-H13 steel nitrogen-implanted samples in low oxygen partial pressure atmosphere. The samples were implanted in a high vacuum chamber by using a broad ion beam source. The  $H_2^+/N_2^+$  ion composition of the beam was varied and the surface composition studied in situ by photoemission electron spectroscopy (XPS). The samples were also ex situ analyzed by X-ray diffraction and scanning electron microscopy (SEM), including energy-dispersive spectroscopy measurements. It was found that hydrogen has the effect of modifying the amount of retained nitrogen at the surfaces. This result shows that hydrogen plays a role beyond the well-established effect of oxygen etching in industrial machines where vacuum is relatively less well controlled. Finally, an optimum concentration of 20–40%  $[H_2]/[H_2+N_2]$  ion beam composition was determined to obtain maximum nitrogen incorporation on the metal surface.

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### 1. Introduction

Plasma nitriding is a well-established technique broadly applied to improve surface properties of steels [1]. Nevertheless, some important physical mechanisms involved in the process are still not well understood. Indeed, the microscopic mechanisms in nitriding processes and their effects on the metal structure continue to be an important subject of study [2–4]. The use of hydrogen in plasma nitriding is a standard procedure to increase nitrogen penetration in steel [5]. The presence of stable oxides on the surface blocks nitrogen diffusion and the beneficial effect of hydrogen attributed to etching effects on the oxides compounds. However, the role of hydrogen is sometimes suggested to go beyond the chemical etching effects. Moreover, some authors claim that the presence of hydrogen

has effects on the plasma structure, influencing nitrogen incorporation in the bulk of the metal [6,7]. Therefore, to observe specific effects of hydrogen, experiments in an oxygen-free atmosphere are mandatory.

In this paper we report a comprehensive nitriding study of AISI-H13 steel in accurately controlled conditions. The samples were implanted in a high vacuum chamber (partial pressure  $<2 \times 10^{-5}$  Pa) by using a Kaufman cell fed with different nitrogen–hydrogen mixtures. The deposition chamber is attached to an ultrahigh vacuum chamber for in situ photoemission electron spectroscopy analysis (XPS) for composition and structural analysis. Also, the structure evolution of the material was studied by ex situ X-ray diffraction. Morphology studies, by ex situ SEM analysis, shows the nitrogen diffusion via grain boundaries. Experimental results show that 20–40% hydrogen partial pressure increases nitrogen concentration in the metal bulk. This experimental finding confirms that hydrogen plays a role beyond the well-established oxygen etching.

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## 56 2. Experimental

57 The samples studied in the present work are rectangular  
58 ( $20 \times 15 \times 2$  mm) slices from the same AISI-H13 steel lot.  
59 Table 1 displays the material composition as determined  
60 by XPS analysis in sputtered cleaned raw samples. The  
61 nitriding process was performed on a high vacuum system  
62 with a base pressure always better than  $2 \times 10^{-5}$  Pa  
63 ( $P[\text{O}_2] < 10^{-6}$  Pa) using a Kaufman cell. This system is  
64 attached to a UHV chamber where in situ X-ray photo-  
65 electron spectroscopy (XPS) measurements are performed.  
66 More details of the implanting system can be found  
67 elsewhere [8]. To carry out this study, all system  
68 parameters were maintained constant and the hydrogen  
69 and nitrogen flux proportion accurately adjusted. These  
70 gases are admitted into the Kaufman cell through  
71 independent mass flow controllers. The hydrogen partial  
72 pressure,  $C_H = [\text{H}_2]/[\text{N}_2 + \text{H}_2]$ , was varied from 0 to 80 at.%  
73 maintaining fixed the total chamber pressure ( $\sim 1.4 \times 10^{-2}$   
74 Pa). Other important parameters maintained constant  
75 during ion implantation are: ion beam energy, 600 eV;  
76 ion beam effective current density:  $2 \text{ mA/cm}^2$  (measured  
77 with a faraday cup); temperature:  $450 \text{ }^\circ\text{C}$ ; implantation  
78 time: 2 hours. At this energy, both nitrogen and hydrogen  
79 will be dissociated and shallow implanted [2,9,10]. Indeed,  
80 SRIM simulations show that at 300 eV, nitrogen and  
81 hydrogen will reach 1 and 5 nm depths, respectively [11].  
82 These characteristic depths show that a thin oxide layer  
83 may indeed be an efficient barrier for nitrogen incorpo-  
84 ration and diffusion. Moreover, hydrogen passivation on  
85 this first 5 nm layer might increase both, nitrogen  
86 retention (up to saturation concentrations) and mobility  
87 (through alloying elements traps screening) [12]. Finally,  
88 after the nitriding process, the samples are transferred to  
89 the ultrahigh vacuum chamber ( $< 5 \times 10^{-7}$  Pa) for XPS  
90 measurements.

91 The neutral species contained in the beam are difficult to  
92 measure. However, we can make an attempt to estimate their  
93 concentrations. Conservation laws forbid neutralization of  
94 the ions in the gas phase at the working pressures used in the  
95 present study [13]. Therefore, the origin of the neutral  
96 species in the beam could stem from two sources: (1)  
97 neutralization due to electrons injected by the filament  
98 neutralizer of the Kaufman cell, and (2) secondary electrons  
99 emitted due to ion impact on grounded parts of the Kaufman  
100 cell. In the experimental conditions reported in this paper  
101 the beam neutralizer was not used. Therefore, this contri-  
102 bution to the formation of neutral species is not present.  
103 Regarding secondary electron emission, it can be neglected.

Indeed, the secondary emission coefficient of 100 eV  $\text{N}_2^+$  104  
ions hitting molybdenum is  $\gamma \sim 0.032$  [14,15]. Considering 105  
that  $\gamma$  weakly depends on energy, one can estimate that at 106  
most  $\sim 3.2\%$  of the  $\text{N}_2^+$  ion will be neutralized in the ion 107  
beam. The XPS spectra were obtained by using the 1486.6 108  
eV photons from an Al target ( $\text{K}\alpha$ -line) and a VG-CLAMP- 109  
2 electron analyzer. The total apparatus resolution was  $\sim 0.85$  110  
eV (line-width plus analyzer). The relative atomic compo- 111  
sition at the sample surfaces was determined by integrating 112  
the core level peaks, properly weighted by the photo- 113  
emission cross-section. As is well known, XPS gives 114  
information of the outmost atomic material layers ( $\sim 0.5$  115  
nm) [16]. Crystallographic information was acquired with 116  
the usual  $\theta$ - $2\theta$  mode X-ray diffraction (XRD) with the Cu 117  
 $\text{K}\alpha$ -line. Material hardness measurements were performed 118  
using a standard Vickers micro-indenter (0.05 kg load, 119  
Shimadzu) and the morphological characterization by a 120  
scanning electron microscopy (SEM) (Jeol JMS-5900LV), 121  
equipped with energy dispersive spectrometry (EDS). The 122  
samples for SEM measurements were mirror-polished and 123  
120 seconds etched in 2% nital solution. SEM images and 124  
EDS were obtained using 8 keV electron beam energy and 125  
15 keV, respectively. 126

## 3. Results and discussion 127

### 3.1. Influence of the $\text{H}_2/[\text{H}_2 + \text{N}_2]$ gaseous mixture on 128 surface composition and hardness 129

Fig. 1(a) shows the nitrogen and iron concentrations 130  
obtained from XPS studies as a function of hydrogen 131  
partial pressures in the Kaufman cell in the absence of 132  
oxygen. This plot shows the nitrogen dependence retention 133  
on the surface material by the presence of  $\text{H}_2^+$  in the ion 134  
beam. The curves show that a maximum (minimum) 135  
nitrogen (iron) concentration at the surfaces is obtained 136  
for 30–40% (20–30%)  $\text{H}_2/[\text{H}_2 + \text{N}_2]$  gaseous mixtures. This 137  
indicates that even if the plasma nitriding process takes 138  
place in a very low oxygen partial pressure chamber, some 139  
hydrogen will enhance nitrogen surface retention. The 140  
observed diminishing N concentration above around 30– 141  
40% gaseous concentration is probably due to chemical 142  
etching. Also, the increment of hydrogen partial pressure 143  
decreases the effective nitrogen ionic current, contributing 144  
to a lower nitrogen concentration on the surface. Fig. 1(b) 145  
displays surface hardness vs. gaseous mixture. Within the 146  
experimental error, hydrogen slightly reduces hardness to 147  
an almost constant value, independent of gas mixture 148  
composition. As we shall see below, however, the 149  
crystalline structure depends on the gaseous mixture. 150  
Finally, it is important to remark that the oxygen 151  
concentration measured by XPS on the surfaces was 152  
smaller than 3 at.% for all studied samples. This is 153  
expected since XPS analyses were performed in situ in a 154  
high vacuum chamber. 155

t1.1 Table 1  
t1.2 AISI H13 steel composition, at.%

t1.3 Element	Fe	C	Mn	Si	Cr	Mo	V
t1.4 Concentration ( $\pm 0.5$ at.%)	90.5	0.6	0.3	0.3	6.7	1	0.7

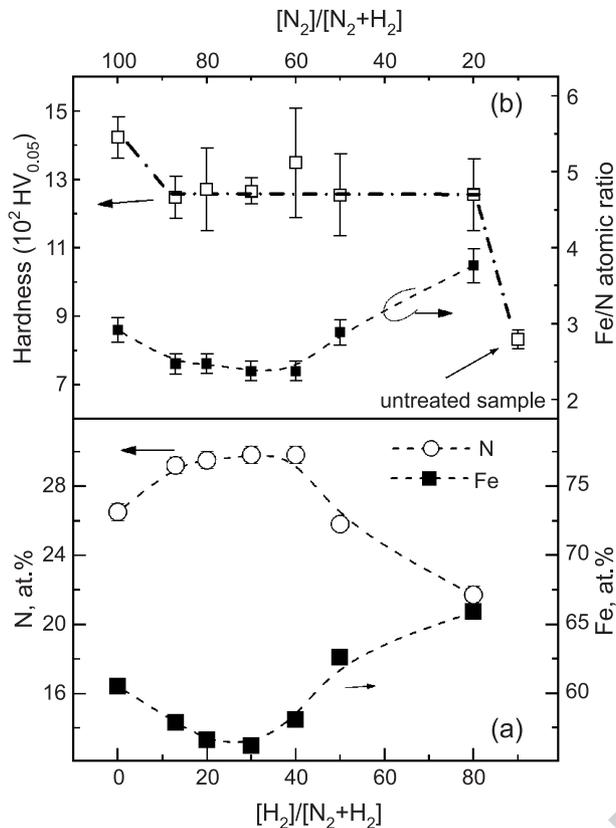


Fig. 1. (a) Nitrogen and iron surface concentration as function of gaseous nitrogen concentration feeding the ion source. (b) Frontal hardness and iron/nitrogen ratio as function of gaseous nitrogen concentration feeding the ion source. Lines are guide to the eyes.

### 3.2. Influence of the $H_2/[H_2+N_2]$ gaseous mixture on the material structure

The X-ray diffraction patterns of the studied samples are enlightening about the phases present in the material. Fig. 2 shows the evolution of the crystalline material on N incorporation. A pristine sample is also included for comparison purposes. Except for sample  $H_2-80$ , implanted with 80%  $H_2/[H_2+N_2]$  gaseous mixture, the  $\epsilon$ -phase ( $Fe_2-3N$ ) is sizable in all curves [17,18]. The  $\alpha$ -phase (bcc) is also apparent as a shoulder in some nitrated samples. The presence of these phases is consistent with the iron/nitrogen stoichiometry obtained from the XPS data after subtracting nitrogen bounded to alloying elements (see Fig. 1b). The constituent alloying elements (Cr, V, Mo) produces two effects: stabilization of the original  $\alpha$ -phase and more retention of nitrogen in the structure [19]. In fact, depending on the nitrogen concentration, two phenomena are possible. On the one hand, at relative low N content, the  $\alpha$ -phase is predominant and N does not exceed the solubility limit of the element in the Fe-N binary system [20]. On the other hand, at higher N content, the  $\epsilon$ -phase becomes dominant. Thus, the presence of the  $\alpha$ -phase observed in different samples even at nitrogen concentration above the solubility limit suggests non-equilibrium nitrogen over saturated  $\alpha$ -

phase. X-ray diffraction also reveals that samples treated with less hydrogen are more expanded (not shown) possibly explaining the greater hardness of sample  $H_2-00$ .

The photoelectron emission spectra (XPS) of the allowing elements, such as Cr2p3/2 and V2p3/2, show the onset of a second peak. For chromium this second peak, associated with  $Cr_{1+x}N$  ( $x$  near to 0), has a chemical shift of  $\sim 1.1$  eV and is responsible for  $\sim 40\%$  of the total signal independently of the  $[H_2]/[N_2+H_2]$  mixture feeding the ion source [21]. For the sake of clarity, only the results obtained with  $[H_2]/[N_2+H_2]=50\%$  are displayed in Fig. 3(a). We remark that the curve asymmetry is due to shake-up process [16]. Assuming that, after nitrogen incorporation, two bands associated to chromium environments, where used to fit the curves (see Fig. 3). The first band corresponds to the N1s core electrons of nitrogen-free material and the second one to the electrons associated to N1s core electrons in chromium nitrides compounds. The latest contribution is chemically shifted due to the electronegative effect of

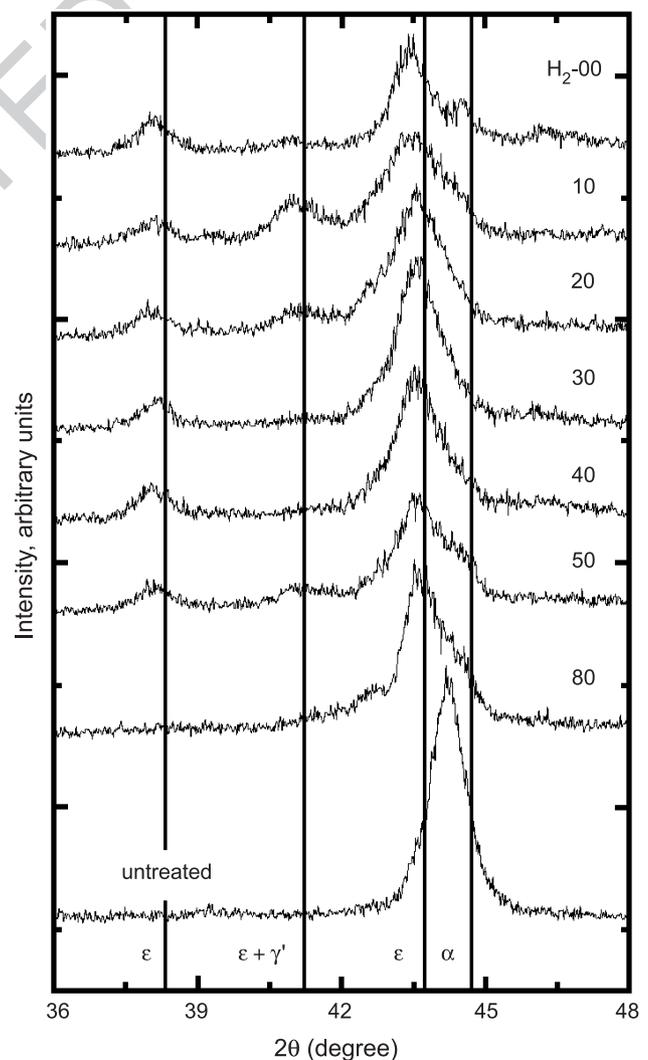


Fig. 2. X-ray diffractogram of nitrated samples. The characteristic position of  $\epsilon$ -,  $\gamma'$ - and  $\alpha$ -phases are indicated.

199 nitrogen [16]. Similar results are obtained for all studied  
 200 gaseous mixtures. Also, we note that the chemical shift to  
 201 higher energies observed in the photoemission electron core  
 202 level binding energies is consistent with the high N  
 203 electronegativity. The photoelectron emission spectrum  
 204 associated with the N1s electron is a broad band centered  
 205 at  $\sim 394.4$  eV (Fig. 3b). This band (width  $\sim 1.9$  eV) is  
 206 constituted by electrons stemming from contributions of  
 207 several metallic nitrides such as CrN, VN, MoN, and Fe<sub>2-</sub>  
 208 <sub>4</sub>N. We note that this band overlaps with the one associated  
 209 with the spectrum of the Mo3p<sub>3/2</sub> electron core level. In Fig.  
 210 3, a 10% contribution stemming from the Mo p<sub>3/2</sub> core  
 211 electron (not shown) has been properly subtracted.

### 212 3.3. Morphology

213 Fig. 4 shows the SEM result (backscattered mode)  
 214 obtained in sample H<sub>2</sub>-50 taken from its transversal cross  
 215 section. Several features are observed in this picture. First,  
 216 the dark zones around grain boundaries near the surface  
 217 indicate the presence of light nuclear density elements such  
 218 as N. Therefore, grain boundary diffusion through the

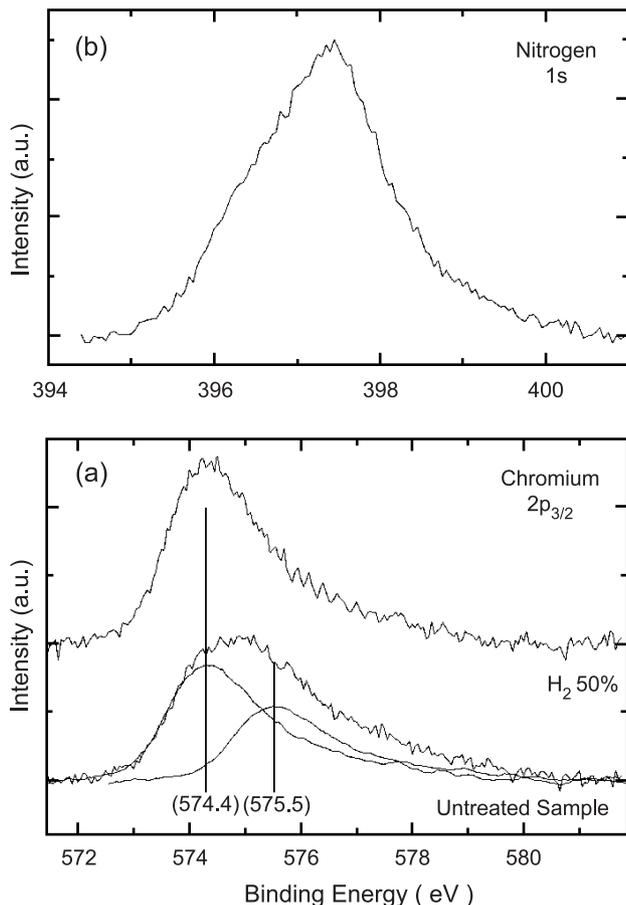


Fig. 3. (a) Spectra corresponding to the Cr2p<sub>3/2</sub> photoelectrons for untreated and nitrided samples with 50% hydrogen feeding the ion source. It can be observed the onset of a second band, 1.1 eV chemical shifted toward increasing binding energies. (b) N 1s band formed by contribution stemming from all N chemical states.

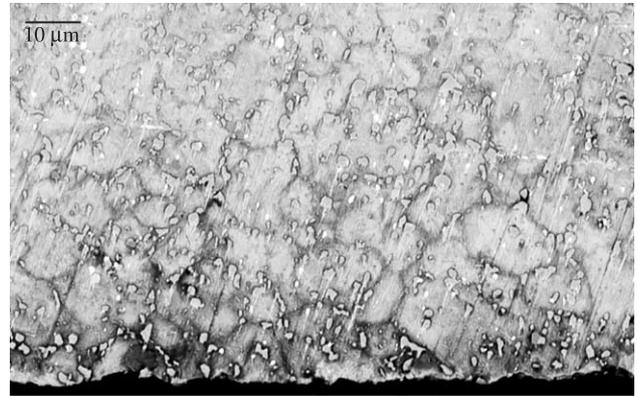


Fig. 4. SEM image in backscattered configuration (sample N50). The dark grain contours are evidences of nitrogen presence. The bright smallest spot are metallic precipitates.

219 presence of defects of N is strongly suggested for the  
 220 picture, explaining the relative thick diffusion layer for this  
 221 sample ( $\sim 30$  μm). Second, the small bright spots indicate  
 222 metallic nitrides precipitates. The higher density of these  
 223 spots at the outmost layers of the samples is due to higher N  
 224 concentrations near the sample surfaces. At the surface,  
 225 therefore, the large amount of precipitates suggests a  
 226 composition bulk grain change by alloying elements  
 227 depletion. In order to verify this hypothesis, spatially  
 228 resolved energy-dispersed X-ray spectroscopy (EDS) was  
 229 performed at the borders and bulk region of sample grains.  
 230 In particular, the probed zone was located at the outmost  
 231 sample layers and deeper in the studied samples. At the  
 232 outmost layers, the EDS results confirm the increasing  
 233 (decreasing) alloying elements, such as Cr and V, at the  
 234 grain boundary (bulk) as compared with normal concen-  
 235 tration found in deeper material layers. This is understood  
 236 because N extracts allowing element from the bulk grains to  
 237 form the precipitates, depleting the bulk of the grains near  
 238 the material surfaces. Unfortunately, SEM pictures of the  
 239 studied samples do not show sizable differences in samples  
 240 treated with diverse H<sub>2</sub>/[H<sub>2</sub>+N<sub>2</sub>] mixtures. However, the  
 241 effect observed on N retention is probably due to the  
 242 formation of hydrides at the grain boundary, playing an  
 243 important role in the diffusion process [21–23].

### 244 4. Conclusion

245 In conclusion, in this work we have shown that, at very  
 246 low oxygen partial pressure ( $< 2 \times 10^{-6}$  Pa), appropriated  
 247 nitrogen dilution in hydrogen improves nitrogen retention at  
 248 the surface of the material. This results shows that hydrogen  
 249 has a specific role going beyond that of the well-established  
 250 oxygen etching. Depending on the nitrogen concentration,  
 251 two phenomena can occur. First, for relative low N  
 252 concentration, the  $\alpha$ -phase is stabilized. Second, at higher  
 253 N surface retention, the  $\epsilon$ -phase is formed. Scanning  
 254 electron microscopy confirms that N diffuses by grain

255 boundary. Moreover, metallic nitrite precipitates blocks N  
 256 diffusion deeper in the bulk material. The presence of H  
 257 neutralizes allowing components potentially acting as N  
 258 traps. Finally, the incorporation of H to the ion beam slightly  
 259 reduces the material hardness as compared the material  
 260 implanted with a pure  $N_2^+$  ion beam and influences the  
 261 formed crystalline structure.

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 269 LME/LNLS, Campinas.

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